# Zero Bias Anomaly in the Absence of Equilbrium

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### OUTLINE

- Two types of ZBA
- Tunnelling current in a non-equilibrium case
- Tunnelling DoS or else?

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# Why "anomaly"?

Ohm's law:

 $\frac{\mathrm{d}I}{\mathrm{d}V} = \frac{1}{R} \equiv G \qquad \begin{array}{l} \text{Normal:} \\ G = \text{const} \end{array}$ 

Expected "anomaly": "Unexpected" anomaly: "high" voltage
low voltage (bias), V→0

At low T

well-known

for ages

A. Sommerfeld and H. Bethe, <u>Handbuch der Physik</u>, edited by H. Geiger and K. Scheel (Verlag von Julius Springer, Berlin, 1933), Vol. 24, Pt. 2, p. 450.

### Two types of ZBA

ZERO-BIAS ANOMALIES IN NORMAL METAL TUNNEL JUNCTIONS

PHYSICAL REVIEW LETTERS

J. M. Rowell and L. Y. L. Shen Bell Telephone Laboratories, Murray Hill, New Jersey Volume 17, Number 1 4 July 1966





FIG. 3. Dynamic resistance versus voltage for Ta-I-Al and Ta-I-Ag junctions at  $0.9^{\circ}$ K. A field of 3 kG was used to drive the tantalum normal.

FIG. 1. (a) The dynamic resistance versus voltage for a Cr-I-Ag junction at 0.9°K. The voltage scales are A = 0.2 mV/division, B = 1.0 mV/division, C = 5 mV/division, D = 20 mV/division. (b) The dynamic resistance versus voltage for a Cr-I-Ag junction at various temperatures. E = 0.9, F = 20.4, G = 77, and  $H = 290^{\circ}$ K. The voltage scale is 10 mV/division.

### **Dependence on disorder**

Zero-Bias Anomaly in Irradiated Pb-GaAs Tunnel Junctions, and the Mott Transition\*



Nabih A. Mora, Stuart Bermon, and J. J. Loferski

PHYSICAL REVIEW LETTERS Volume 27, Number 10 6 September 1971

conjecture – Mott transition (DoS goes to 0 in its vicinity). In general: disorder matters

FIG. 2. Voltage dependence of the normalized conductance  $G(V)/G_b(V)$  at  $1.42^{\circ}$ K for junction 8B-4 after successive neutron irradiations. The integrated neutron flux is (1) 0; (2) 0.6; (3) 2.8; (4) 5.9; (5) 12.1; (6) 18.3; (7) 24.5, all in units of  $10^{16} n/\text{cm}^2$ .

### **Dependence on T and V**



FIG. 1. Tunneling conductance vs voltage for five 2D samples (measured at 1.2 K) and typical resistance vs temperature for two of these samples (see Table I for sample identification). Inset depicts the low-bias I-V characteristics of sample b with the Pb electrode superconducting (curve s) and in the presence of 1 kOe magnetic field.

PHYSICAL REVIEW LETTERS

VOLUME 49, NUMBER 11

13 September 1982

Density-of-States Anomalies in a Disordered Conductor: Yoseph Imry<sup>(a)</sup> IBM Research Center, Yorktown Heights, New York 10598

Zvi Ovadyahu<sup>(b)</sup> Brookhaven National Laboratory, Upton, New York 11973

### Excellent log dependence – in an agreement with (then) new theory:

PHYSICAL REVIEW LETTERS Volume 44, Number 19 12 May 1980

Interaction Effects in Disordered Fermi Systems

B. L. Altshuler A. G. Aronov P. A. Lee

### **Disorder+Interaction ⇒ "miniblockade"**

Scatterting from impurities creates self-returning trajectories



The lower dimension d, the higher return probability

This **disorder-driven** effect makes tunnelling more difficult for an additional electron **interacting** with the rest

$$\begin{split} \overbrace{\mathbf{f}_{\text{deal}}}_{\text{probe}} & \overbrace{\mathbf{f}_{\text{disordered sample}}}^{\text{Interacting}} & \mathcal{H} = \mathcal{H}_{\text{P}} + \mathcal{H}_{\text{S}} + \mathcal{H}_{\text{T}} \\ \mathcal{H}_{\text{T}} = & \int \gamma(\mathbf{r}) \psi_{\text{P}}^{\dagger}(\mathbf{r}) \psi_{\text{S}}(\mathbf{r}) \, \mathrm{d}^{d}\mathbf{r} + \text{h.c.} \\ \mathcal{H}_{\text{T}} = & \int \gamma(\mathbf{r}) \psi_{\text{P}}^{\dagger}(\mathbf{r}) \psi_{\text{S}}(\mathbf{r}) \, \mathrm{d}^{d}\mathbf{r} + \text{h.c.} \\ integration over the contact volume} \\ \mathcal{I}(t) = & -e\dot{N}_{\text{P}} = -\frac{ie}{\hbar} \langle [H_{\text{T}}, N_{\text{P}}] \rangle = -\frac{ie\gamma}{\hbar} \int \mathrm{d}^{d}r \Big[ \left\langle \psi_{\text{P}}^{\dagger}(\mathbf{r}, t) \psi_{\text{S}}(\mathbf{r}, t) \right\rangle - \text{h.c.} \Big] \\ & = \frac{e\gamma}{\hbar} \int \mathrm{d}^{d}r \Big[ G_{\text{PS}}^{<}(\mathbf{r}, \mathbf{r}; t, t) - G_{\text{SP}}^{<}(\mathbf{r}, \mathbf{r}; t, t) \Big] \\ \hat{G} \equiv \begin{pmatrix} G^{++} & G^{<} \\ G^{>} & G^{--} \end{pmatrix} & - \text{Keldysh' Green's function, with} \\ G^{++}(1, 1') \equiv -i \left\langle \hat{T}\psi(1)\psi^{\dagger}(1') \right\rangle \\ G^{++} + G^{--} = G^{<} + G^{>} \end{split}$$

- Express  $\hat{G}_{PS} = \hat{G}_{P}^{0} \hat{\gamma} \hat{G}_{S}$  via  $G_{P}$  and  $G_{S}$
- Substitute  $H_{P,S} \rightarrow H_{P,S} (\mu H)_{P,S}$
- Bias  $\mu_{\mathsf{P}} \rightarrow \mu_{\mathsf{S}} + eV$
- Use the perfectness of P:  $G_{\rm P}^{<}(\varepsilon) = 2\pi i f_{0}(\varepsilon) v_{\rm P}(\varepsilon)$
- Rotate Keldsyh G:  $G^{\text{R,A}} = G^{\text{--}} G^{\text{--}}, \quad G^{\text{K}} \equiv G^{\text{--}} + G^{\text{--}}$  $\mathcal{I} = \frac{i\pi e \widetilde{\gamma}^2}{\hbar} \int_{-\infty}^{\infty} \frac{\mathrm{d}\varepsilon}{2\pi} \Big\{ \nu_{\text{P}}(\varepsilon - eV) \Big[ G_{\text{S}}^{\text{K}}(\boldsymbol{r}, \boldsymbol{r}; \varepsilon) \\ -h_0(\varepsilon - eV) \Big( G_{\text{S}}^{\text{R}} - G_{\text{S}}^{\text{A}} \Big)(\boldsymbol{r}, \boldsymbol{r}; \varepsilon) \Big] \Big\}$

 $h \equiv 1 - 2f;$  Keldysh ansatz:  $G^{K}{}_{S} = H_{S}(G^{R} - G^{A})_{S}$  $G^{R} - G^{A} = 2\pi i A(r, \varepsilon) \rightarrow LDoS;$  no information on distribution all purely non-equilibrium effects are in  $G^{K}{}_{S}$ 

## Two contributions to ${\mathcal I}$

Differentiate  $\mathcal{J}$  to find  $d\mathcal{J}/dV = (d\mathcal{J}/dV)_1 + (d\mathcal{J}/dV)_2$ :

$$\left( \frac{\mathrm{d}\mathcal{I}}{\mathrm{d}V} \right)_1 = \frac{1}{2R_T} \int \mathrm{d}\varepsilon \, \frac{\nu_{\mathrm{S}}(\varepsilon)}{\overline{\nu}_{\mathrm{S}}} \frac{\partial}{\partial \varepsilon} h_0(\varepsilon - eV) \approx \frac{\nu_{\mathrm{S}}(eV)}{\overline{\nu}_{\mathrm{S}} R_T}$$

Main contribution (smeared by T)  $1/R_T = (2\pi e^2/\hbar) \widetilde{\gamma}^2 \overline{\nu}_P \overline{\nu}_S$ 

Additional contribution: ( $\widetilde{\varepsilon} \equiv \varepsilon + eV$ )

$$\left(\frac{\mathrm{d}\mathcal{I}}{\mathrm{d}V}\right)_2 = \frac{1}{2R_T \overline{\nu}_{\mathbf{P}}} \int \mathrm{d}\varepsilon \, \frac{\partial \nu_{\mathbf{P}}(\varepsilon)}{\partial \varepsilon} \left[h_0(\varepsilon) - H_{\mathbf{S}}(\widetilde{\varepsilon})\right] A_S(\widetilde{\varepsilon}, \boldsymbol{r})$$

Two conditions for the existence:

probe DoS is non-flat near  $\mathcal{E}_{F}$ H<sub>S</sub> differs essentially from h<sub>0</sub>

# **Tunnelling DoS contribution**



In the diffusive limit,

$$\lambda_{\mathrm{F}}, \kappa^{-1} \ll \ell \ll L,$$

1<sup>st</sup> order correction in the inter-n is enough

is universal (no dependence on int.strength at  $\omega \ll D\kappa q$ )

$$\frac{\delta\nu(\bar{\epsilon})}{\nu_0} = -\frac{\hbar}{16\pi E_F \tau} \left\{ \ln\left(\frac{\bar{\epsilon}a_B^4}{\hbar D^2 \tau}\right) \ln(\bar{\epsilon}\tau/\hbar) + 2\left[\ln(\tau\Delta/\hbar)\right]^2 \right\}$$

Altshuler, Aronov, Lee, 1980

Rudin, Aleiner, Glazman, 1997

# **Non-equilibrium distribution**

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FIG. 1. Experimental layout: a metallic wire of length L is connected at its ends to reservoir electrodes, biased at potentials 0 and U. In the absence of interaction, the distribution function at a distance X = xL from the grounded electrode has an intermediate step f(E) = 1 - x for energies between -eU and 0 (solid curves) (we assume U > 0).

 $\frac{1}{\tau_{\rm D}} \frac{\partial^2 f(x,\varepsilon)}{\partial x^2} + \operatorname{St}(x,\varepsilon) = 0$ 

In the absence of relaxation (St=0),  $f(\mathcal{E})$  is a double-step:

 $f_0(x,\varepsilon) = (1-x) f_0(\varepsilon + eU) + x f_0(\varepsilon)$ 

P are superconducting:  $\nu_{\mathbf{P}}(\varepsilon) = \overline{\nu} / \sqrt{\varepsilon^2 - \Delta^2}$ 

ZBA is suppressed; the 2<sup>nd</sup> contribution to  $\mathcal{I}$  is measured giving information on f (and St) and thus on relaxation processes.

### Measuring f with "zero-bias" probe

A. Anthore, F. Pierre\*, H. Pothier, D. Esteve, and M. H. Devoret





### General results:

$$\begin{split} \frac{\mathrm{d}\mathcal{I}^{\mathrm{add}}}{\mathrm{d}V} &= \frac{\tau_{esc}}{\overline{\nu}R_T} \int \mathrm{d}\varepsilon \, \frac{\partial\nu_{\mathrm{P}}(\varepsilon)}{\partial\varepsilon} \, \mathrm{St}(\varepsilon \!+\! eV) \\ \mathrm{St}(\varepsilon) &= -\frac{1}{2\pi\nu_d(\varepsilon)} \int \frac{\mathrm{d}\varepsilon'}{2\pi} \int \frac{\mathrm{d}\omega}{2\pi} K(\varepsilon, \varepsilon', \omega) \\ &\times \Big\{ \big[ h(t, \varepsilon' - \omega) - h(t, \varepsilon') \big] \big[ 1 - h(t, \varepsilon - \omega)h(\varepsilon) \big] \\ &- \big[ h(t, \varepsilon - \omega) - h(t, \varepsilon) \big] \big[ 1 - h(t, \varepsilon' - \omega)h(t, \varepsilon') \big] \Big\} \\ \mathrm{At \ equilibrium \ (h=h_0), \ St=0.} \end{split}$$

Results for a double-step f and a Breit-Wigner DoS of the probe  $(\partial \nu / \partial \epsilon \propto \delta(\epsilon))$ :

 $-\left(\frac{\mathrm{d}\mathcal{I}}{\mathrm{d}V}\right)_{2} = \frac{\tau_{\mathrm{esc}}}{\overline{\nu}R_{\mathrm{T}}} \times \begin{cases} \left(g_{1}\sqrt{2\tau_{\mathrm{D}}U}\right)^{-1}\varphi_{1}(\varepsilon/U), \\ \text{quasi-1d} \\ (1/2g_{2})\varphi_{2}(\varepsilon/U), \end{cases}$ 

The singularity is smeared out by temperature  $T \ll U$ 



2d

# Summary

 For non-equilibrium *f*, tunnelling current at small V is governed by the standard tunnelling DoS singularity and by a singular kinetic term proportional to St

• Kinetic contribution may be dominant, and is controllable by changing the escape time